74AHC1G14-Q100; 74AHCT1G14-Q100

Inverting Schmitt trigger

Rev. 2 — 18 January 2016

Product data sheet

1. General description

74AHC1G14-Q100 and 74AHCT1G14-Q100 are high-speed Si-gate CMOS devices. They provide an inverting buffer function with Schmitt-trigger action. These devices can transform slowly changing input signals into sharply defined, jitter-free output signals.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - \bullet MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- SOT353-1 and SOT753 package options

3. Applications

- Wave and pulse shapers
- Astable multivibrators
- Monostable multivibrators



4. Ordering information

Table 1. Ordering information

Type number	Package	Package										
	Temperature range	Name	Description	Version								
74AHC1G14GW-Q100	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1								
74AHCT1G14GW-Q100			body width 1.25 mm									
74AHC1G14GV-Q100	−40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753								
74AHCT1G14GV-Q100												

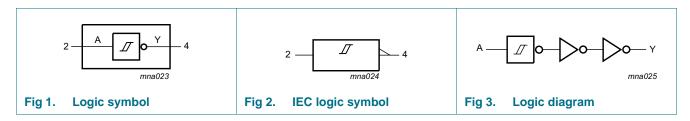
5. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74AHC1G14GW-Q100	AF
74AHCT1G14GW-Q100	CF
74AHC1G14GV-Q100	A14
74AHCT1G14GV-Q100	C14

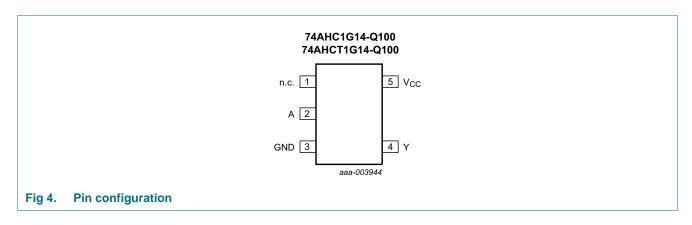
^[1] The pin 1 indicator is on the lower left corner of the device, below the marking code.

6. Functional diagram



7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description		
n.c.	1	not connected		
Α	2	data input		
GND	3	ground (0 V)		
Υ	4	data output		
V _{CC}	5	supply voltage		

8. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Input	Output
A	Υ
L	Н
Н	L

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V	-20	-	mA
I _{OK}	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	75	mA
I _{GND}	ground current		−75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	-	250	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For both TSSOP5 and SC-74A packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AF	74AHC1G14-Q100			74AHCT1G14-Q100		
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C

11. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
For type	74AHC1G14-Q	100								
V _{OH}	HIGH-level	$V_I = V_{T+}$ or V_{T-}								
	output voltage	$I_{O} = -50 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu A; V_{CC} = 3.0 \text{ V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_I = V_{T+}$ or V_{T-}								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
Cı	input capacitance		-	1.5	10	-	10	-	10	pF
For type	74AHCT1G14-	Q100				1	l		1	
V _{OH}	HIGH-level	$V_{I} = V_{T+} \text{ or } V_{T-}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_{I} = V_{T+} \text{ or } V_{T-}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ

74AHC_AHCT1G14_Q100

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Table 7. Static characteristics ... continued

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C		-40 °C to +85 °C		-40 °C t	Unit		
			Min	Тур	Max	Min	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
Δl _{CC}	additional supply current	per input pin; V_I = 3.4 V; other inputs at V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance		-	1.5	10	-	10	-	10	pF

11.1 Transfer characteristics

Table 8. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V). See Figure 7 and Figure 8.

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
For type	74AHC1G14-Q1	00	,						'	
V _{T+}	positive-going	V _{CC} = 3.0 V	-	-	2.2	-	2.2	-	2.2	V
	threshold voltage	V _{CC} = 4.5 V	-	-	3.15	-	3.15	-	3.15	V
		V _{CC} = 5.5 V	-	-	3.85	-	3.85	-	3.85	V
V_{T-}	negative-going	V _{CC} = 3.0 V	0.9	-	-	0.9	-	0.9	-	V
	threshold voltage	V _{CC} = 4.5 V	1.35	-	-	1.35	-	1.35	-	V
		V _{CC} = 5.5 V	1.65	-	-	1.65	-	1.65	-	V
V _H	hysteresis	V _{CC} = 3.0 V	0.3	-	1.2	0.3	1.2	0.25	1.2	V
	voltage	V _{CC} = 4.5 V	0.4	-	1.4	0.4	1.4	0.35	1.4	V
		V _{CC} = 5.5 V	0.5	-	1.6	0.5	1.6	0.45	1.6	V
For type	74AHCT1G14-G	1100	,						'	
V _{T+}	positive-going	V _{CC} = 4.5 V	-	-	2.0	-	2.0	-	2.0	V
	threshold voltage	V _{CC} = 5.5 V	-	-	2.0	-	2.0	-	2.0	V
V_{T-}	negative-going	V _{CC} = 4.5 V	0.5	-	-	0.5	-	0.5	-	V
threshold voltage	V _{CC} = 5.5 V	0.6	-	-	0.6	-	0.6	-	V	
V_{H}	hysteresis	V _{CC} = 4.5 V	0.4	-	1.4	0.4	1.4	0.35	1.4	V
	voltage	V _{CC} = 5.5 V	0.4	-	1.6	0.4	1.6	0.35	1.6	V

12. Dynamic characteristics

Table 9. Dynamic characteristics

GND = 0 V; $t_f = t_f \le 3.0$ ns. For waveform see <u>Figure 5</u>. For test circuit see <u>Figure 6</u>.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
For type	74AHC1G14	-Q100									
t _{pd}	propagation	A to Y;	[1]								
	delay	V _{CC} = 3.0 V to 3.6 V	[2]								
		C _L = 15 pF		-	4.2	12.8	1.0	15.0	1.0	16.5	ns
		C _L = 50 pF		-	6.0	16.3	1.0	18.5	1.0	20.5	ns
		V _{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	3.2	8.6	1.0	10.0	1.0	11.0	ns
		C _L = 50 pF		-	4.6	10.6	1.0	12.0	1.0	13.5	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$; $f = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	12	-	-	-	-	-	pF
For type	74AHCT1G1	4-Q100					1		-	1	
t _{pd}	propagation delay	A to Y; V _{CC} = 4.5 V to 5.5 V	[1] [3]								
		C _L = 15 pF		-	4.1	7.0	1.0	8.0	1.0	9.0	ns
		C _L = 50 pF		-	5.9	8.5	1.0	10.0	1.0	11.0	ns
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC}	<u>[4]</u>	-	13	-	-	-	-	-	pF

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \sum (C_L \times V_{CC}{}^2 \times f_o)$$
 where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in Volts.

^[2] Typical values are measured at $V_{CC} = 3.3 \text{ V}$.

^[3] Typical values are measured at $V_{CC} = 5.0 \text{ V}$.

13. Waveforms

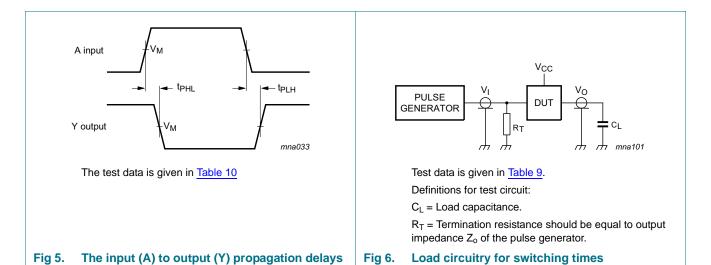
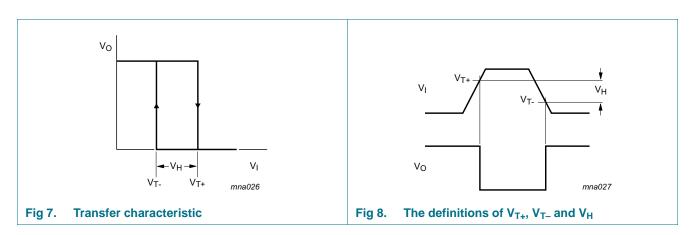


Table 10. Test data

Type number	Input	Output	
	VI	V _M	V _M
74AHC1G14-Q100	GND to V _{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT1G14-Q100	GND to 3.0 V	1.5 V	$0.5 \times V_{CC}$

13.1 Transfer characteristic waveforms



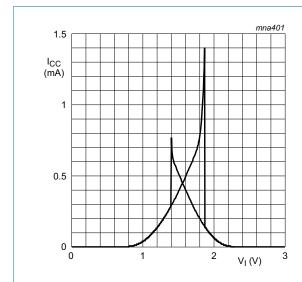


Fig 9. Typical 74AHC1G14-Q100 transfer characteristics; V_{CC} = 3.0 V

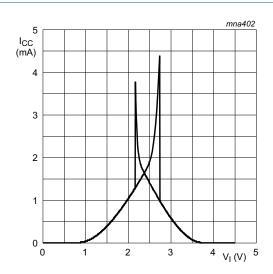


Fig 10. Typical 74AHC1G14-Q100 transfer characteristics; V_{CC} = 4.5 V

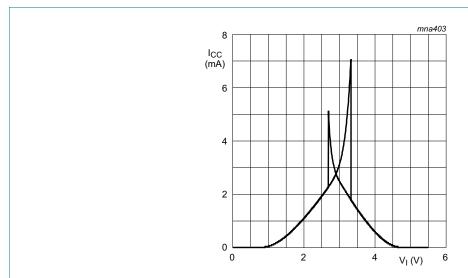
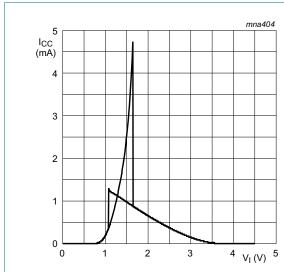


Fig 11. Typical 74AHC1G14-Q100 transfer characteristics; V_{CC} = 5.5 V





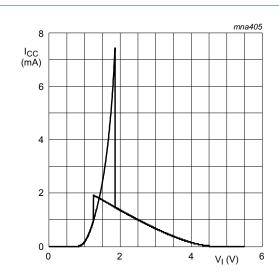


Fig 13. Typical 74AHCT1G14-Q100 transfer characteristics; V_{CC} = 5.5 V

14. Application information

The slow input rise and fall times cause additional power dissipation, which can be calculated using the following formula:

 $P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC}$ where:

 P_{add} = additional power dissipation (μW);

 $f_i = input frequency (MHz);$

 t_r = input rise time (ns); 10 % to 90 %;

 t_f = input fall time (ns); 90 % to 10 %;

 $\Delta I_{CC(AV)}$ = average additional supply current (μA).

Average additional I_{CC} differs with positive or negative input transitions, as shown in Figure 14 and Figure 15.

For 74AHC1G14-Q100 and 74AHCT1G14-Q100 used in relaxation oscillator circuit, see Figure 16.

Note to the application information:

1. All values given are typical unless otherwise specified.

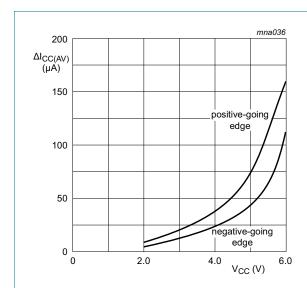


Fig 14. Average additional I_{CC} for 74AHC1G14-Q100 Schmitt-trigger devices; linear change of V_I between 0.1 V_{CC} to 0.9 V_{CC}

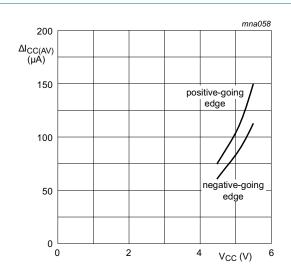
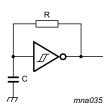


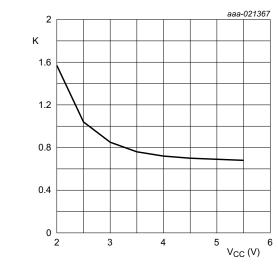
Fig 15. Average additional I_{CC} for 74AHCT1G14-Q100 Schmitt-trigger devices; linear change of V_I between $0.1V_{CC}$ to $0.9V_{CC}$



For 74AHC1G14-Q100 and 74AHCT1G14-Q100: $f = \frac{1}{T} \approx \frac{1}{K \times RC}$

For K-factor, see Figure 17

Fig 16. Relaxation oscillator using the 74AHC1G14-Q100 and 74AHCT1G14-Q100



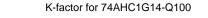
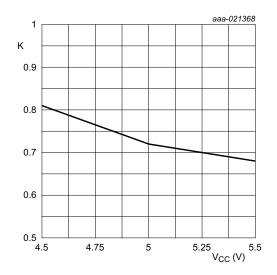


Fig 17. Typical K-factor for relaxation oscillator



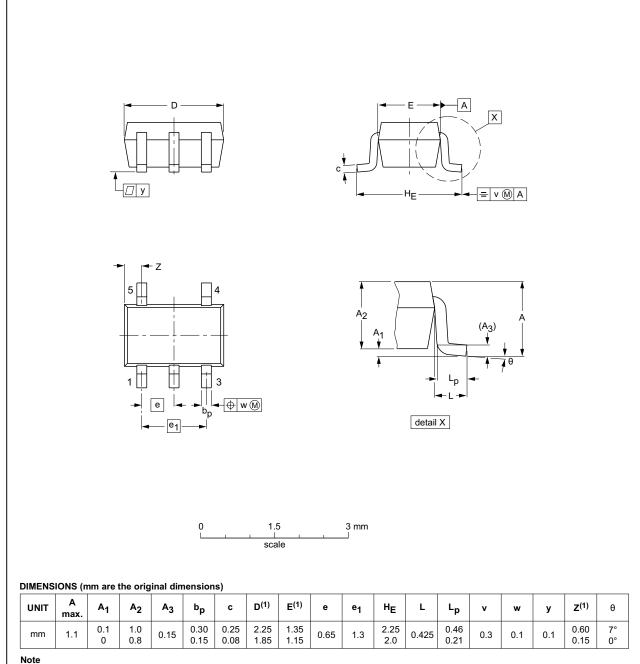


K-factor for 74AHCT1G14-Q100

15. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



11016

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT353-1		MO-203	SC-88A			-00-09-01 03-02-19	

Fig 18. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

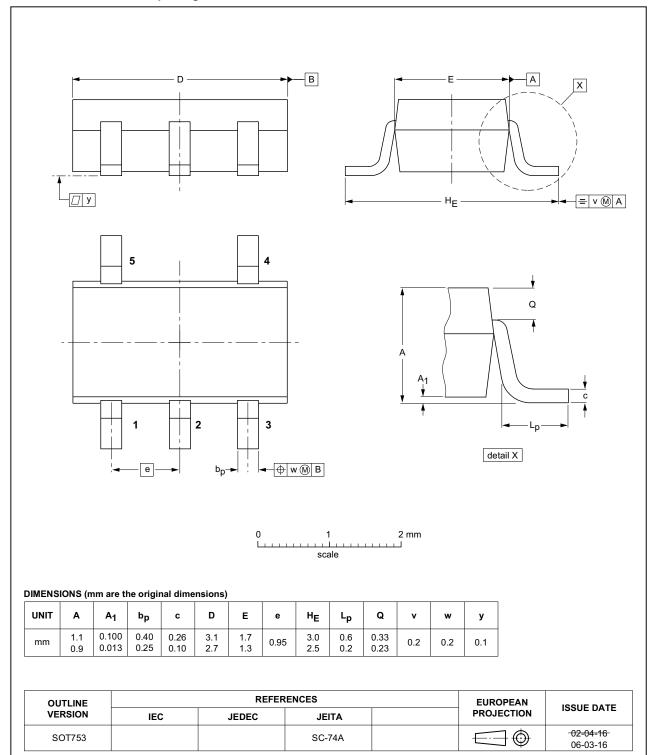


Fig 19. Package outline SOT753 (SC-74A)

16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT1G14_Q100 v.2	20160118	Product data sheet	-	74AHC_AHCT1G14_Q100 v.1
Modifications:	Figure 17 added (typical K-factor for relaxation oscillator).			
74AHC_AHCT1G14_Q100 v.1	20120713	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors 74AHC1G14-Q100; 74AHCT1G14-Q100

Inverting Schmitt trigger

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20. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Ordering information	2
5	Marking	2
6	Functional diagram	2
7		2
7.1	Pinning	2
7.2		3
8	Functional description	3
9	Limiting values	3
10	Recommended operating conditions	4
11	Static characteristics	4
11.1	Transfer characteristics	5
12	Dynamic characteristics	6
13	Waveforms	
13.1	Transfer characteristic waveforms	7
14	Application information	9
15	Package outline 1	2
16	Abbreviations 1	4
17	Revision history 1	4
18	Legal information 1	5
18.1		5
18.2	Definitions	5
18.3		5
18.4	Trademarks 1	6
19	Contact information 1	6
20	Contents 1	7

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